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# A model to describe surface physics in EUVL optics mirror contamination

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This work has been performed as a METI project  
under the management of NEDO

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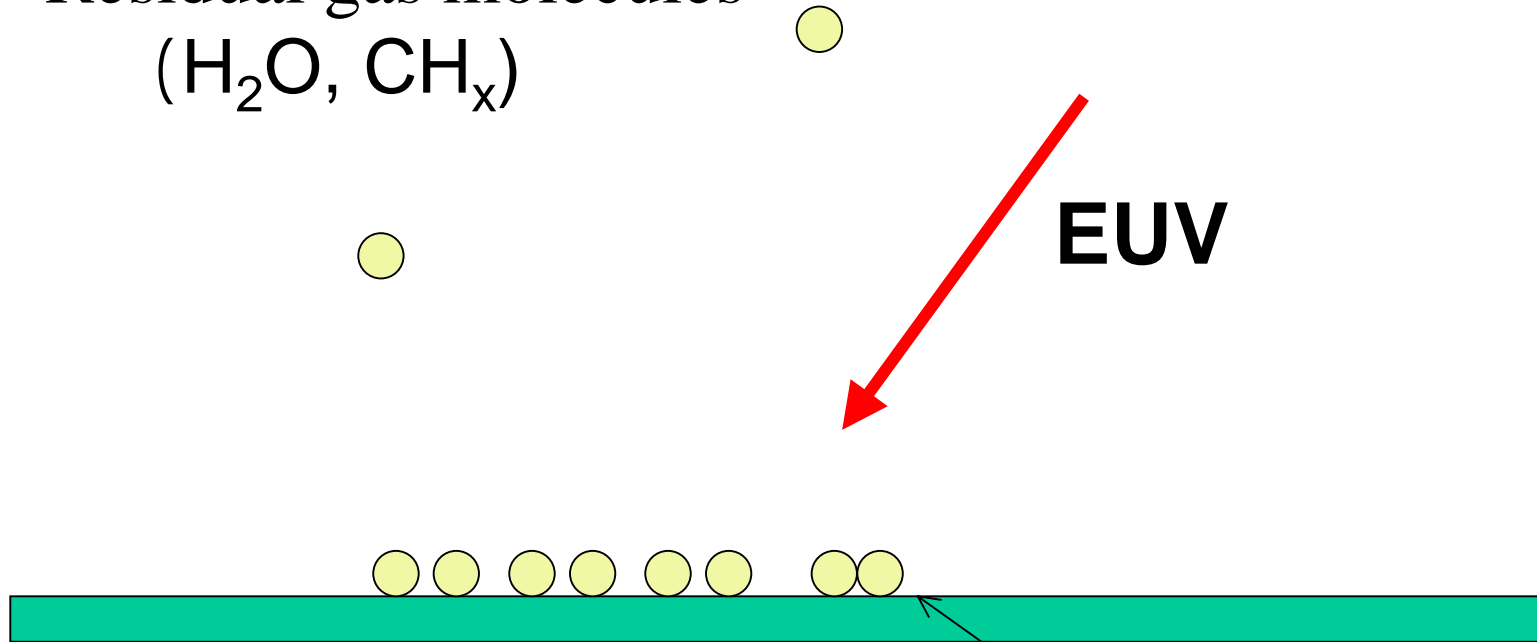
## Background

Multilayer (ML) mirror of projection optics in EUVL tools is oxidized by the influence of  $H_2O$  in residual gases and carbon deposition may also take place. Resultantly, EUV reflection rate is reduced.

## Purpose

To propose a model to describe surface physics in mirror contamination, analyze the condition of acceleration test, and estimate whether or not we have difference in irradiation results between pulse and more continuous irradiation conditions.

Residual gas molecules  
( $\text{H}_2\text{O}$ ,  $\text{CH}_x$ )



$\text{H}_2\text{O}$ : dissociated and to oxidize  
 $\text{CH}_x$ : decomposed

ML mirror surface

Adsorption of residual gas species is described by

$$d\sigma_i/dt = S_i\Gamma_i - \sigma_i/\tau_i - \eta_i P \quad (1)$$

$\sigma_i$ : surface areal density of i-th residual gas molecules (/cm<sup>2</sup>)

$S$ : sticking probability

$\Gamma$ : arriving rate of residual gas molecules (/cm<sup>2</sup>.s)

$$\Gamma = n_i v_{thi}/4$$

$\tau$ : mean residence time (s)

$\eta$ : photon-induced desorption coefficient (molecules/photon)

$P$ : EUV photon flux (/cm<sup>2</sup>.s)

When  $P$  is large, the second term can be neglected.

In continuous irradiation, steady state is given by

$$S_i \Gamma_i = \eta_i P \quad (2)$$

In pulse irradiation,

$$S_i \Gamma_i \Delta t_f = \eta_{mi} P_{mp} \Delta t_p \quad (3)$$

$\Delta t_f / \Delta t_p$ : pulse-to-pulse/pulse duration,  $P_p$ : pulse power

Photon-induced desorption is expressed by

$$\eta_i = \eta_{i0} (\sigma_i / \sigma_{i0})^n \quad (4)$$

$\eta_{i0}$  is  $\eta_i$  @  $\sigma_{i0}$ . In both cases, using mean power  $P_m$

$$\sigma_{im} = \sigma_{i0} (S_i \Gamma_i / P_m \eta_{i0})^{1/n} \quad (5)$$

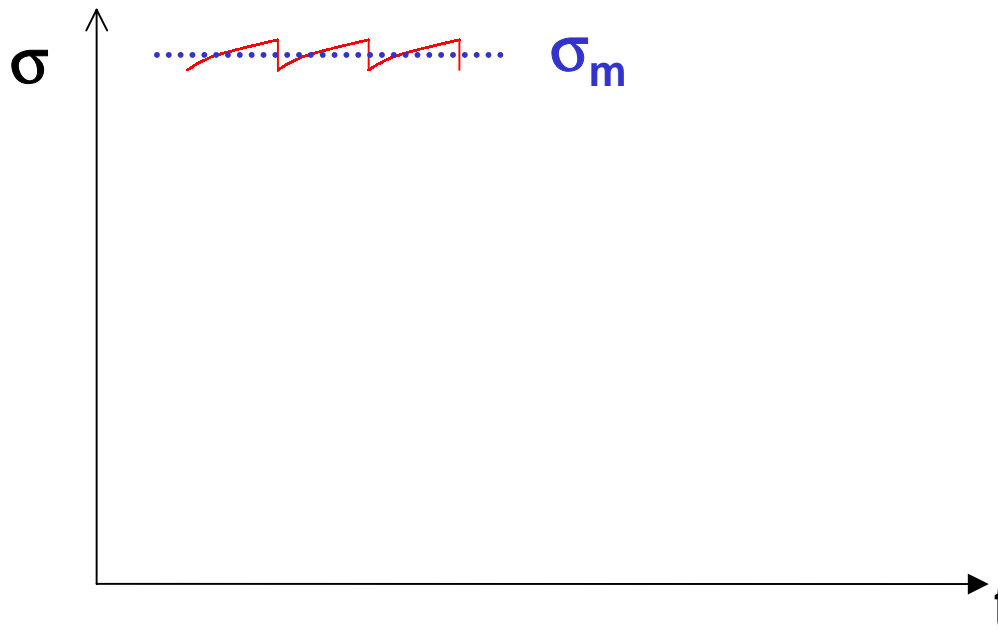
We assume that EUV-exited process is proportional to  $\int P\sigma_i dt$ . Using Eq. (5),

$$\int P\sigma_i dt \propto \Gamma_i^{1/n} P^{(1-1/n)}, \quad (6)$$

suggesting that if we increase  $P$  by a factor of  $M$ , we should also increase  $\Gamma_i$  or the corresponding residual gas pressure by  $M$ .

This is somewhat obvious from Eq. (2) or (3). Namely,  $\sigma_i$  does not change in this condition, and  $\int P\sigma_i dt$  is resultantly proportional to  $P$ .

If the condition  $\sigma_{im} \gg S_i \Gamma_i \Delta t_f$  is satisfied, it implies that difference between pulse and more continuous operation is small. This is because the arriving quantity during the pulse is so much smaller than the existing amount on the surface.



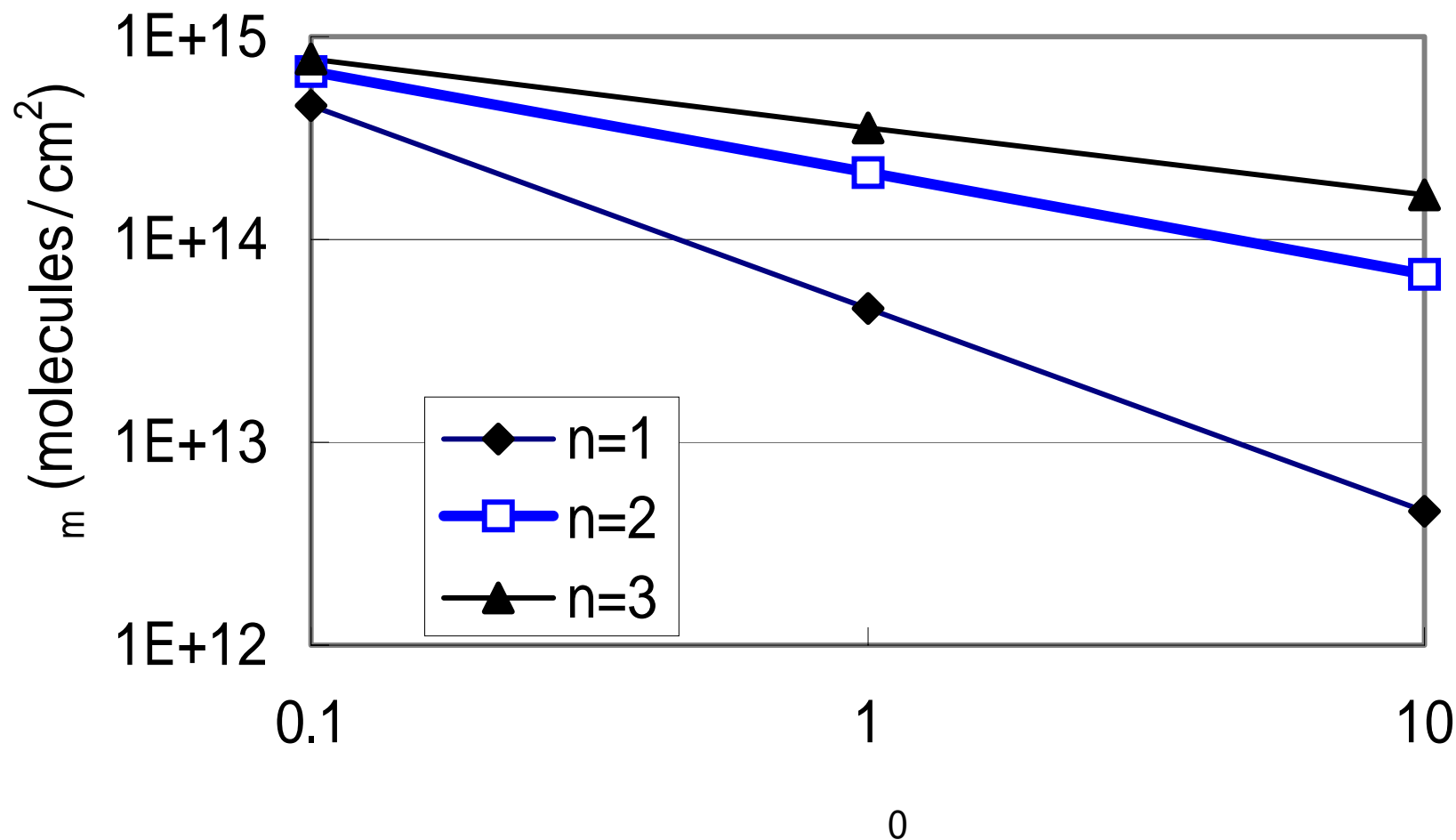
Assuming a pulse frequency of 10kHz, mean EUV irradiation power ( $P_m$ ) of 20mW/cm<sup>2</sup> which should be converted to photon flux, H<sub>2</sub>O pressure of 3x10<sup>-5</sup> Pa and S=0.5, the arriving quantity during the pulse is given as

$$S\Gamma\Delta t_f = 6.2 \times 10^9 \text{ (molecules/cm}^2\text{)}.$$

The existing amount on the surface is estimated by Eq. (5) which is

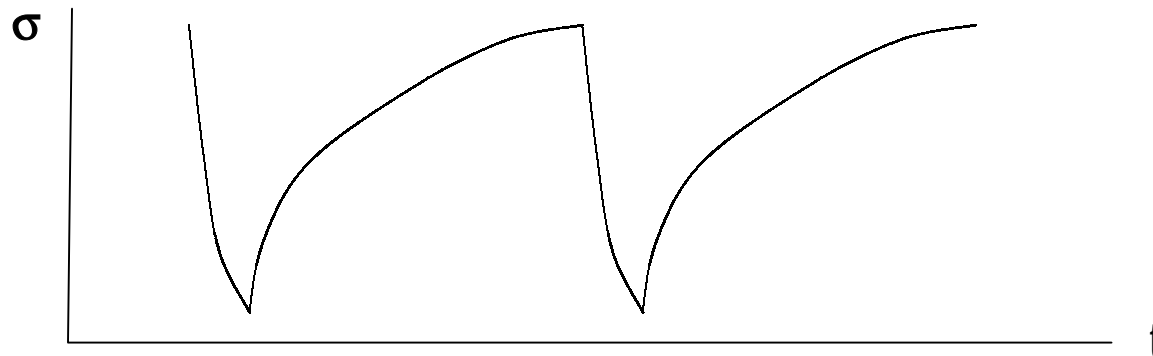
$$\sigma_i = \sigma_{i0} (S_i \Gamma_i / P_m \eta_{i0})^{1/n}, \quad (5)$$

taking  $\eta_{i0}$  and n as parameters.



$\eta_0$  is the value for monolayer ( $\sigma_0=10^{15}$  molecules/cm<sup>2</sup>)

The condition  $\sigma_{im} \gg S_i \Gamma_i \Delta t_f$  is satisfied with a margin of more than 3 orders of magnitude. **Thus, the author concludes that the difference between pulse and more continuous operations is quite small.** When do we have difference?



This happens when (1) the pulse frequency is small and (2) the corresponding residual gas pressure is high.

The surface physics model tells:

- In acceleration test, the pressure of the corresponding gas should be increased proportionally to the photon intensity increase.
- Pulse irradiation in EUVL tools can be simulated by using more continuous irradiation.

Acknowledgement to:

EUVA: T. Aoki, H. Kondo, S. Matsunari, H. Takase, S. Terashima

Univ. Hyogo: Y. Kakutani, M. Niibe